## Table of contents

Chapter 1: Introduction	1
1.1. Background and scope of study	1
1.2. Aim and objectives	5
1.3. Thesis structure	6
Chapter 2: Literature Review	8
2.1.1 Discovery of ZnO nanobelts (2001)	8
2.1.2 Growth of aligned ZnO nanowires (2004–2005)	
2 1 3 Doping of ZnO nanostructures	
2.2. Fundamental properties and theoretical models.	
2.2.1. Crystal structure of ZnO	
2.2.2. Optical properties	
2.2.2.1. Band-gap engineering of ZnO	17
2.2.2.2. Burstein-Moss effect	
2.2.3. Photoluminescence	19
2.2.3.1. Surface effects on photoluminescence properties	
2.2.4. Vibrational properties and Raman spectroscopy	
2.2.5. Field Electron Emission	
2.2.5.1. Fowler-Nordheim Plot (F-N Plot)	29
Chapter 3: Experimental methods and instrumentation	31
3.1. Thermal evaporation method	31
3.1.1. Conventional thermal evaporation set-up	32
3.1.2. Modification of thermal evaporation set-up	
3.2. Epitaxial growth of nanostructures	35
3.2.1. Vapor-Liquid-Solid (VLS) method	
3.2.2. Vapor-Solid (VS) method	43
3.2.3. Different morphologies of 1D ZnO nanostructures	43
3.3. Instrumentation	45
3.3.1. Field Emission Scanning Electron Microscope (FESEM) and Energy Disp X-Ray (EDX)	ersive 46

3.3.2. Transmission Electron Microscope (TEM) and Select Area Electron Diffraction
(SAED)
3.3.3. X-Ray Diffraction (XRD)
3.3.4. Auger electron spectroscopy (AES)
3.3.5. Photoluminescence and Raman spectroscopies
3.3.6. Field emission measurements
Chapter 4: Fabrication and characterization of un-doped ZnO nanowires
4.1. Introduction
4.2. Experimental details
4.3. Growth and characterization of ZnO nanowires using a conventional thermate evaporation set-up
4.4. Growth and characterization of ZnO nanowires using a modified thermal evaporation set-up
4.4.1.Source temperature effect on morphological properties of ZnO nanowires grown using a modified thermal evaporation set-up
Chapter 5: Fabrication and characterization of doped-ZnO nanowires
5.1. Introduction
5.2. Growth and characterization of ZnO <sub>x</sub> Mg <sub>1-x</sub> O nanowires80
5.2.1. Growth of Zn <sub>x</sub> Mg <sub>1-x</sub> O nanowires using a conventional set-up
5.2.1.1. Experimental details
5.2.1.2. Results and discussion
5.2.2. Growth of Zn <sub>x</sub> Mg <sub>1-x</sub> O nanowires using a modified set-up
5.2.2.1. Experimental details
5.2.2.2. Results and discussion
5.2.3. Field emission study of Zn <sub>1-x</sub> Mg <sub>x</sub> O nanowires
5.3. Al-doped ZnO nanowires using AlN thin films
5.3.1. Experimental details
5.3.2. Results and discussion
5.4. Growth of ZnO/ZnInO heterostructure nanowires
5.4.1. Experimental details
5.4.2. Results and discussion
Chapter 6: Growth and doping of ZnO nanobelts126

6.1. Introduction	126
6.2. S- and Sn-doped ZnO nanobelts	126
6.2.1. Experimental details	126
6.2.2. Results and discussion	127
6.3. The effects of annealing temperature on structural and optical properties of	of S-doped
ZnO nanobelts	136
Charten 7. Canalasiana	1 / 1
Chapter /: Conclusions	141
Appendix A	144
A.1. List of Publication	144
A.2. Internationl Conference Attendent	145
Bibliography	146

## **List of Figures**

Figure 1. 1. Worldwide ZnO consumption per continent
Figure 1.2. Publication statistics on nanostructures for ZnO. The data were received on May 20, 2009 through the Institute of Scientific Information (ISI) database using the following key words that appear in the title, abstracts, and keywords: ZnO (or zinc oxide) together with nanowire, nanobelt, nanorod, nanoribbon, nanotip, nanofiber, nanoring, nanohelix, nanospring, nanobrush, or nanoflower
Figure 1.3. A summary of ZnO applications and properties
Figure 1.4. The map of physics adopted from Physics World
Figure 2.1. TEM images of the as-synthesized ZnO nanobelts
Figure 2.2. SEM images of (a) single-crystal nanospring, (b) nanoring, and (c) superlattice structured nanohelix of ZnO9
Figure 2.3. Aligned ZnO nanowire arrays that were grown on a sapphire surface10
Figure 2.4. Stick and ball representation of ZnO crystal structures: (a) cubic rocksalt $(B_1)$ , (b) cubic zinc blende $(B_3)$ , and (c) hexagonal wurtzite $(B_4)$ . The shaded gray and black spheres denote Zn and O atoms, respectively
Figure 2.5. The hexagonal wurtzite structure of ZnO16
Figure 2.6. Schematic of the band-gap in (a) a pure state and (b) a doped state19
Figure 2.7. Schematic of the typical PL process
Figure 2.8. Radiative recombination process: (a) band to band, (b) donor to valance band, (c) conduction band to acceptor, (d) donor to acceptor, and (e) non-radiative process via an intermediate state
Figure 2.9. Schematic band diagram of DLEs in ZnO nanostructures based on the full potential linear muffin-tin orbital method and reported data
Figure 2.10. Schematic of the three visible emission processes, which show energy levels of O vacancy in ZnO structure
Figure 2.11. First Brillion zone (BZ) of the wurtzite structure
Figure 2.12. Schematic representation of the atomic displacement of the BZ optical modes in a hexagonal lattice

Figure 2.13. Schematic diagram of different scatterings: (a) Rayleigh scattering, (b) Stokes Raman scattering, and (c) Anti-Stokes Raman scattering. The $v_i$ and $v_f$ indicate the initial and final states, respectively
Figure 3.1. Photographs of the experimental set-up from different points-of-view, including the thermal evaporation system and two mass flow meters, which control gas flow during the experiment based on sccm (standard cubic centimeters per minute), as well as a temperature calibration diagram
Figure 3.2. Schematic of the thermal evaporate deposition system for the synthesis of 1D nanostructures
Figure 3.3. Schematic of the modified set-up used for the growth of ZnO nanowires
Figure 3.4. Schematic illustration of the growth mechanism of Si nanowires
Figure 3.5. Sputtering system (model SPI) that was used in our lab for producing a gold coating on Si wafers
Figure 3.6. FESEM and AFM images of 30 s Au sputtered on a Si (111) substrate after 30 min of thermal annealing at 700 °C
Figure 3.7. ZnO nanowires grown using the VLS method. Au droplets at the tips of these nanowires can be clearly observed
Figure 3.8. Au-Zn phase diagram40
Figure 3.9. Schematic of ZnO nanowire formation by the VLS process
Figure 3.10. A model of ZnO nanowires growth by the VLS method: (a) schematic of the oxidation of Zn islands and nucleation of ZnO at the liquid-solid interface and (b) oxidation of a Zn island through nanorods
Figure 3.11. Typical growth morphologies of 1D ZnO nanostructures and the corresponding facets
Figure 3.12. (a) ZnO nanostructures that were grown using the VS method: (a) ZnO nanowires (b) ZnO nanobelts and dual-nanorings
Figure 3.13. A photograph of the FEI Quanta 200F FESEM with EDX set-up47
Figure 3.14. A photograph of the TEM microscopy unit (Philips CM200)
Figure 3.15. Schematic of the diffraction of an X-rays beam by parallel atomic planes in a crystalline material

Figure 3.16. Basic features of a typical XRD experiment as well as the Siemens D5000 set- up
Figure 3.17. Schematic of a generated Auger electron emission
Figure 3.18. AES, JAMP-9500F set-up in our lab as well as schematic of all process in Auger spectrometer
Figure 3.19. PL and Raman spectrometers set-up, model: Jobin Yvon Horiba HR 800 UV.
Figure 3.20. (a) Instrument used for field electron emission studies, (b) Schematic diagram of the planar diode configuration assembly
Figure 4.1. FESEM images of the ZnO nanowires grown on Si(111) at different temperatures : (a) 700 °C, (b) 550 °C, and (c) 400 °C
Figure 4.2. FESEM images of the ZnO nanowires grown on Si(100) at different temperatures : (a) 700 °C, (b) 550 °C, and (c) 400 °C60
Figure 4.3. (a) XRD patterns of the ZnO nanowires grown on Si(111) at different temperatures. (b) XRD patterns of the ZnO nanowires grown on Si(100) at different temperatures
Figure 4.4. PL spectra of the ZnO nanowires grown on Si(111) at $(a_1)$ 700 °C, $(b_1)$ 550 °C, $(c_1)$ , 400 °C and on Si(100) at $(a_2)$ 700 °C, $(b_2)$ 550 °C, and $(c_2)$ 400 °C62
Figure 4.5. UV emission spectra for various nanowires diameters. A blue-shift from 381 to 375 nm in the peak position of the UV emission is clearly visible as the nanowires diameter decreases
Figure 4.6. Peak intensities of the UV and DLE emission are plotted against the nanowires aspect ratios. The UV emission was more intense in nanowires with small aspect ratios, while the DLE emission dominated in large aspect ratio nanowires
Figure 4.7. (a <sub>1</sub> ) and (a <sub>2</sub> ): Low- and high-magnification FESEM images of ZnO nanowires grown at 650 °C, respectively. (b <sub>1</sub> ) and (b <sub>2</sub> ): Low- and high-magnification FESEM images of ZnO nanowires grown at 600 °C, respectively. (c <sub>1</sub> ) and (c <sub>2</sub> ): Low- and high-magnification FESEM images of ZnO microdiscs grown at 550 °C, respectively
Figure 4.8. Schematic of nanostructures formation along the tube furnace
Figure 4.9. The green arrows show the diffusion of $N_2$ gas along the one-ended tube, starting at the edge of the tube. In addition, the size of the green arrows shows the decrease in $N_2$ gas diffusion along the tube, from the edge to the end of the tube that was placed at the center of the furnace
xvi

Figure 4.10. XRD patterns for the ZnO nanowires and microdiscs that were grown in different temperatures regions: (a) 650 °C, (b) 600 °C, and (c) 550 °C ......70

Figure 4.11. Room temperature PL spectra of the ZnO nanowires and microdiscs that were grown at different temperatures: (a) 650 °C, (b) 600 °C, and (c) 550 °C......71

Figure 4.13. Raman spectra of the ZnO nanowires and microdiscs that were grown at different temperatures: (a) 650 °C, (b) 600 °C, and (c) 550 °C......74

Figure 4.16. XRD patterns of the hexagonal nanowires and nanospears......78

Figure 5.7. Schematic of set-up that used for growth of Zn<sub>1-x</sub>Mg<sub>x</sub>O nanowires ......91

Figure 5.10. Schematic of Zn<sub>1-x</sub>Mg<sub>x</sub>O and ZnO nanowires formation on various substrates

Figure 5.16. XRD pattern of AlN thin film with cubic structure deposited on glass .......106

Figure 5.18. XRD patterns of the ZnO nanowires deposited at (a) 600 °C and (b) 500 °C. XRD pattern of the nanowires grown at 600 °C not only shows ZnO peaks but also presents three peaks at 38.45°, 44.65° and 48.80° which belong to ZnAIO composite.....107

Figure 5.23. (a<sub>1</sub>) A single ZnO/ZnInO heterostructure nanowire grown for 90 min with four spectra taken of four distinct regions along this nanowire: (A) of the tip, (B) of the upper half, (C) of the middle, and (D) of the bottom half regions of the nanowire  $\frac{114}{114}$ 

Figure 5.28. XRD pattern of the source material before evaporation ......119

Figure 6.2. FESEM image and EDX spectrum of the un-doped ZnO nanobelts ......130

## **List of Tables**

 Table. 2.1. Selective material parameters of ZnO
 15